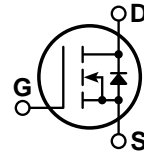
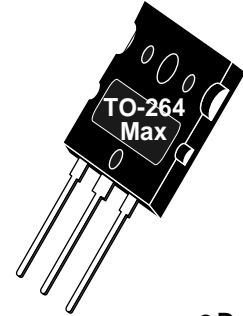


### POWER MOS V®

Power MOS V® is a new generation of high voltage N-Channel enhancement mode power MOSFETs. This new technology minimizes the JFET effect, increases packing density and reduces the on-resistance. Power MOS V® also achieves faster switching speeds through optimized gate layout.



- TO-264 MAX Package
- 100% Avalanche Tested
- Faster Switching
- Lower Leakage

#### MAXIMUM RATINGS

All Ratings:  $T_C = 25^\circ\text{C}$  unless otherwise specified.

| Symbol         | Parameter  | APT10030L2VR | UNIT                |
|----------------|--|--------------|---------------------|
| $V_{DSS}$      | Drain-Source Voltage   | 1000         | Volts               |
| $I_D$          | Continuous Drain Current @ $T_C = 25^\circ\text{C}$            | 33           | Amps                |
| $I_{DM}$       | Pulsed Drain Current <sup>①</sup>                              | 132          |                     |
| $V_{GS}$       | Gate-Source Voltage Continuous                                 | $\pm 30$     | Volts               |
| $V_{GSM}$      | Gate-Source Voltage Transient                                  | $\pm 40$     |                     |
| $P_D$          | Total Power Dissipation @ $T_C = 25^\circ\text{C}$             | 830          | Watts               |
|                | Linear Derating Factor   | 6.64         | W/ $^\circ\text{C}$ |
| $T_J, T_{STG}$ | Operating and Storage Junction Temperature Range               | -55 to 150   | $^\circ\text{C}$    |
| $T_L$          | Lead Temperature: 0.063" from Case for 10 Sec.                 | 300          |                     |
| $I_{AR}$       | Avalanche Current <sup>①</sup> (Repetitive and Non-Repetitive) | 33           | Amps                |
| $E_{AR}$       | Repetitive Avalanche Energy <sup>①</sup>                       | 50           | mJ                  |
| $E_{AS}$       | Single Pulse Avalanche Energy <sup>④</sup>                     | 3200         |                     |

#### STATIC ELECTRICAL CHARACTERISTICS

| Symbol       | Characteristic / Test Conditions   | MIN  | TYP | MAX       | UNIT          |
|--------------|--|------|-----|-----------|---------------|
| $BV_{DSS}$   | Drain-Source Breakdown Voltage ( $V_{GS} = 0V, I_D = 250\mu\text{A}$ )                             | 1000 |     |           | Volts         |
| $I_{D(on)}$  | On State Drain Current <sup>②</sup> ( $V_{DS} > I_{D(on)} \times R_{DS(on)}$ Max, $V_{GS} = 10V$ ) | 33   |     |           | Amps          |
| $R_{DS(on)}$ | Drain-Source On-State Resistance <sup>②</sup> ( $V_{GS} = 10V, 0.5 I_{D(Cont.)}$ )                 |      |     | 0.300     | Ohms          |
| $I_{DSS}$    | Zero Gate Voltage Drain Current ( $V_{DS} = V_{DSS}, V_{GS} = 0V$ )                                |      |     | 25        | $\mu\text{A}$ |
|              | Zero Gate Voltage Drain Current ( $V_{DS} = 0.8 V_{DSS}, V_{GS} = 0V, T_C = 125^\circ\text{C}$ )   |      |     | 250       |               |
| $I_{GSS}$    | Gate-Source Leakage Current ( $V_{GS} = \pm 30V, V_{DS} = 0V$ )                                    |      |     | $\pm 100$ | nA            |
| $V_{GS(th)}$ | Gate Threshold Voltage ( $V_{DS} = V_{GS}, I_D = 5mA$ )  | 2    |     | 4         | Volts         |

 **CAUTION:** These Devices are Sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

APT Website - <http://www.advancedpower.com>

**DYNAMIC CHARACTERISTICS**

**APT10030L2VR**

| Symbol       | Characteristic               | Test Conditions  | MIN | TYP   | MAX | UNIT |
|--------------|------------------------------|--|-----|-------|-----|------|
| $C_{iss}$    | Input Capacitance            | $V_{GS} = 0V$<br>$V_{DS} = 25V$<br>$f = 1\text{ MHz}$  |     | 11170 |     | pF   |
| $C_{oss}$    | Output Capacitance           |  |     | 1010  |     |      |
| $C_{rss}$    | Reverse Transfer Capacitance |  |     | 520   |     |      |
| $Q_g$        | Total Gate Charge ③          | $V_{GS} = 10V$<br>$V_{DD} = 0.5 V_{DSS}$<br>$I_D = 0.5 I_{D[Cont.]} @ 25^\circ C$                  |     | 510   |     | nC   |
| $Q_{gs}$     | Gate-Source Charge           |  |     | 41    |     |      |
| $Q_{gd}$     | Gate-Drain ("Miller") Charge |  |     | 210   |     |      |
| $t_{d(on)}$  | Turn-on Delay Time           | $V_{GS} = 15V$<br>$V_{DD} = 0.5 V_{DSS}$<br>$I_D = I_{D[Cont.]} @ 25^\circ C$<br>$R_G = 0.6\Omega$ |     | 19    |     | ns   |
| $t_r$        | Rise Time                    |  |     | 17    |     |      |
| $t_{d(off)}$ | Turn-off Delay Time          |  |     | 80    |     |      |
| $t_f$        | Fall Time                    |  |     | 12    |     |      |

**SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS**

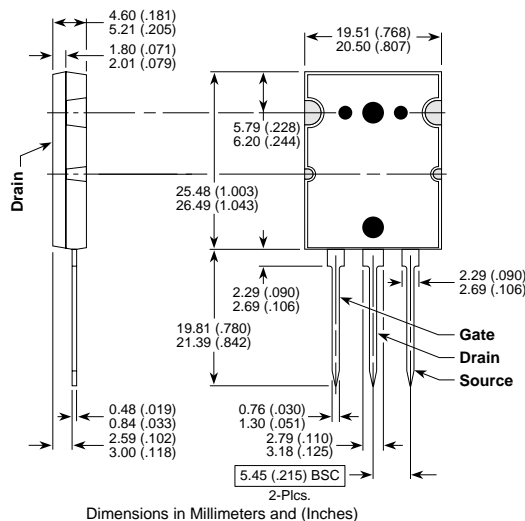
| Symbol   | Characteristic / Test Conditions  | MIN | TYP  | MAX | UNIT    |
|----------|---|-----|------|-----|---------|
| $I_S$    | Continuous Source Current (Body Diode)                                  |     |      | 33  | Amps    |
| $I_{SM}$ | Pulsed Source Current ① (Body Diode)                                    |     |      | 132 |         |
| $V_{SD}$ | Diode Forward Voltage ② ( $V_{GS} = 0V, I_S = -I_{D[Cont.]}$ )          |     |      | 1.3 | Volts   |
| $t_{rr}$ | Reverse Recovery Time ( $I_S = -I_{D[Cont.]}, di_S/dt = 100A/\mu s$ )   |     | 1150 |     | ns      |
| $Q_{rr}$ | Reverse Recovery Charge ( $I_S = -I_{D[Cont.]}, di_S/dt = 100A/\mu s$ ) |     | 31   |     | $\mu C$ |

**THERMAL CHARACTERISTICS**

| Symbol          | Characteristic      | MIN | TYP | MAX  | UNIT         |
|-----------------|---------------------|-----|-----|------|--------------|
| $R_{\theta JC}$ | Junction to Case    |     |     | 0.15 | $^\circ C/W$ |
| $R_{\theta JA}$ | Junction to Ambient |     |     | 40   |              |

- ① Repetitive Rating: Pulse width limited by maximum junction temperature.
  - ② Pulse Test: Pulse width < 380  $\mu s$ , Duty Cycle < 2%
  - ③ See MIL-STD-750 Method 3471
  - ④ Starting  $T_j = +25^\circ C, L = 5.88mH, R_G = 25\Omega, \text{Peak } I_L = 33A$
- APT Reserves the right to change, without notice, the specifications and information contained herein.**

**TO-264 MAX™(L2) Package Outline**



050-5990 rev- 3-2001

APT's devices are covered by one or more of the following U.S.patents: 4,895,810 5,045,903 5,089,434 5,182,234 5,019,522 5,262,336  
5,256,583 4,748,103 5,283,202 5,231,474 5,434,095 5,528,058